

Bulk boron doping and surface carbon coating enabling fast-charging and stable Si anodes: from thin film to thick Si electrodes

Xiang Han^{1,2}, Ziqi Zhang², Huixin Chen³, Linshan Luo², Qiaobao Zhang⁵, Jizhang Chen^{1*},
Songyan Chen^{2*}, and Yong Yang^{4*}

¹*College of Materials Science and Engineering, Nanjing Forestry University, Nanjing 210037, China*

²*Department of Physics, Xiamen University, Xiamen 361005, China*

³*Xiamen Institute of Rare Earth Materials, Haixi Institutes, Chinese Academy of Sciences, Xiamen 361021, China*

⁴*State Key Laboratory for Physical Chemistry of Solid Surfaces, Department of Chemistry, Xiamen University, Xiamen 361005, China*

⁵*Department of Materials Science and Engineering, College of Materials, Xiamen University, Xiamen 361005, China*

Corresponding authors: sychen@xmu.edu.cn (S.Y. Chen); chenjizhang@njfu.edu.cn (J.Z. Chen), and yyang@xmu.edu.cn (Y. Yang)

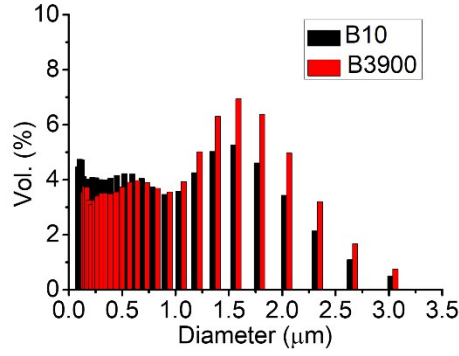


Fig. S1 The diameter distribution of as fabricated boron doped Si powders.

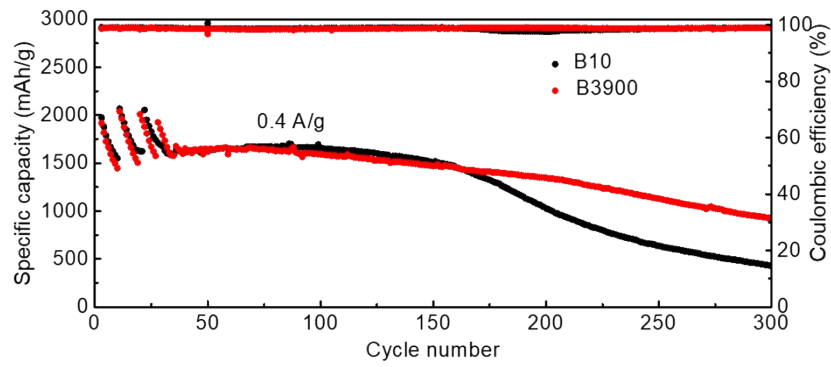


Fig. S2 The cycling performance of carbon coated boron doped Si electrodes at 0.4 A/g.

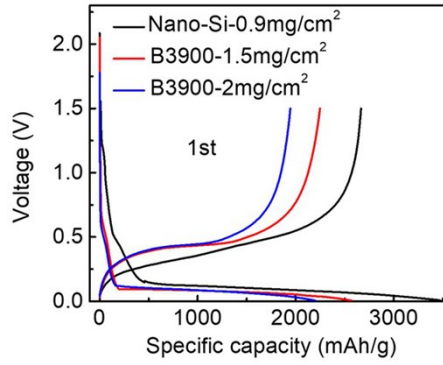


Fig. S3 The initial charge-discharge voltage profiles of Nano-Si, B3900 electrodes.

Table 1. Kinetics parameters of B10 and B3900 electrodes based on EIS data.

Sample	$R_e (\Omega)$	$R_{ct} (\Omega)$	$s (\text{cm}^2 \text{S}^{-0.5})$	$D_{\text{Li}^+} (\text{cm}^2 \text{S}^{-1})$
B10	2.62(4.19%)	13.32(8.89%)	38.78	6.39×10^{-12}
B3900	2.16(1.96%)	7.42(8.41%)	32.69	8.99×10^{-12}

Table 2. The diffusion coefficient evaluated by CV curves.

Sample	Slope	D_{Li^+} (cm ² S ⁻¹)
B10	2.89	1.08×10^{-12}
B3900	7.97	8.24×10^{-12}